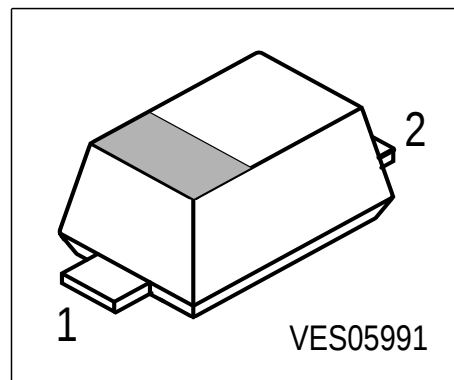


Silicon Tuning Diode

- For SAT-indoor-units
- High capacitance ratio
- Low series inductance
- Low series resistance
- Extremely small plastic SMD package
- Excellent uniformity and matching due to "in-line" matching assembly procedure



Type	Marking	Ordering Code	Pin Configuration	Package
BB 857	O	Q62702-B0897 unmatched	1 = C 2 = A	SCD-80
BB 857	O	Q62702-B0893 inline matched		

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage ($R \geq 5k\Omega$)	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ...+150	°C
Storage temperature	T_{stg}	-55 ...+150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Reverse current $V_R = 30\text{ V}$	I_R	-	-	10	nA
Reverse current $V_R = 30\text{ V}, T_A = 85\text{ }^{\circ}\text{C}$	I_R	-	-	200	
AC characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 25\text{ V}, f = 1\text{ MHz}$ $V_R = 28\text{ V}, f = 1\text{ MHz}$	C_T	6 - 0.45	6.6 0.55 0.54	7.2 - 0.65	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T25}	-	12	-	
Capacitance ratio $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T28}	9.7	12.2	-	
Capacitance ratio ¹⁾ $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	$\Delta C_T/C_T$	-	-	5	%
Series resistance $V_R = 5\text{ V}, f = 470\text{ MHz}$	r_s	-	1.5	-	Ω
Series inductance	L_s	-	0.6	-	nH

1) In-line matching. For details please refer to Application Note 047

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$

